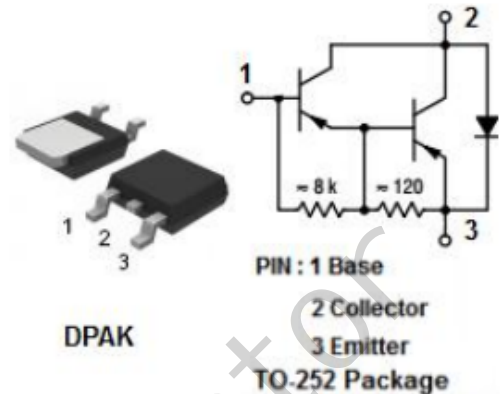


**DESCRIPTION**

- Low Collector-Emitter saturation voltage
- Lead formed for surface mount applications
- High DC current gain
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation


**APPLICATIONS**

- Designed for general purpose amplifier and low speed switching applications.

**ABSOLUTE MAXIMUM RATINGS(T<sub>a</sub>=25°C)**

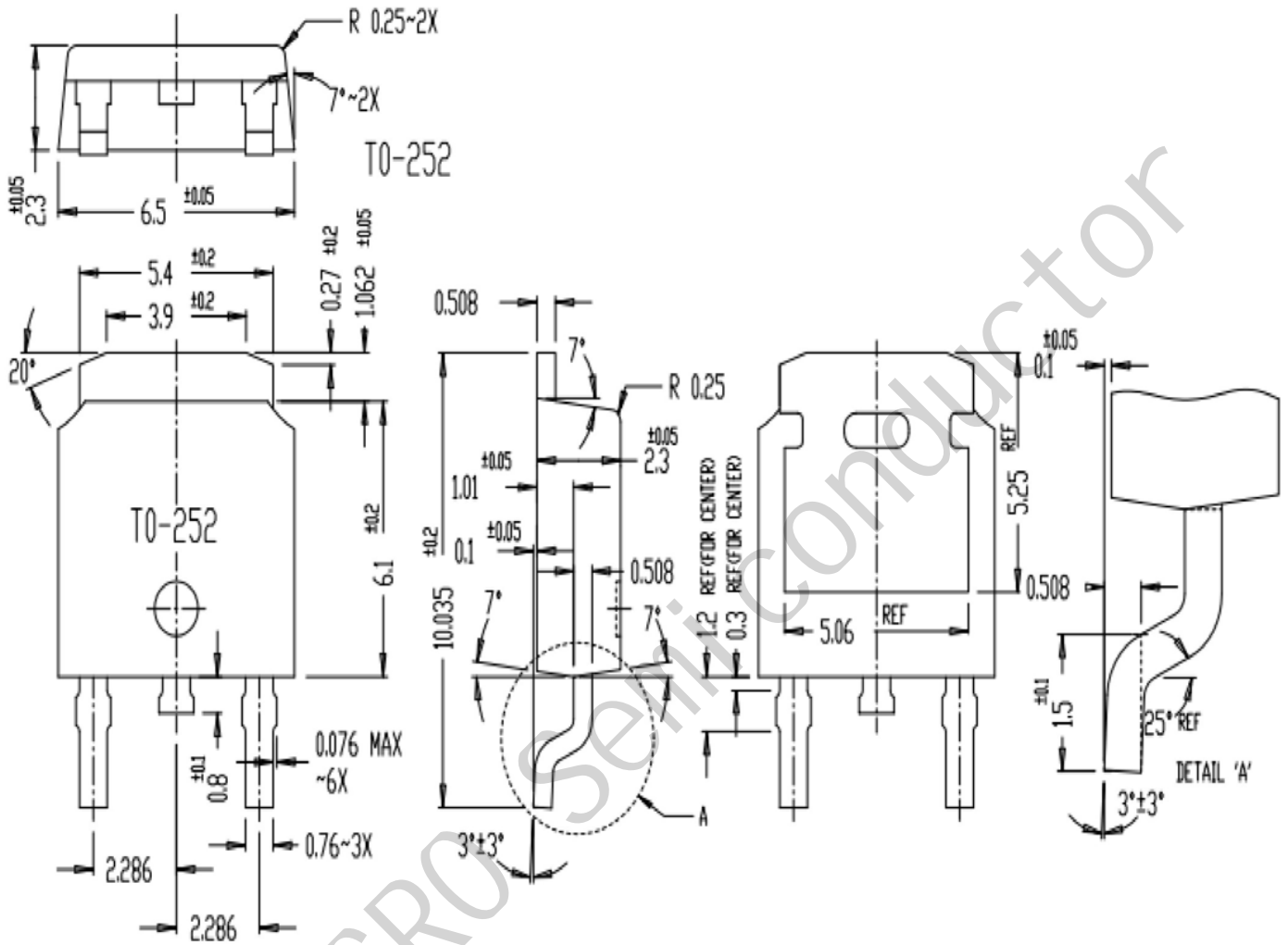
SYMBOL	PARAMETER	VALUE	UNIT
V <sub>CBO</sub>	Collector-Base Voltage	-100	V
V <sub>CEO</sub>	Collector-Emitter Voltage	-100	V
V <sub>EBO</sub>	Emitter-Base Voltage	-5	V
I <sub>C</sub>	Collector Current-Continuous	-8	A
P <sub>C</sub>	Total Power Dissipation @ T <sub>a</sub> =25°C	1.75	W
P <sub>C</sub>	Collector Power Dissipation T <sub>C</sub> =25°C	20	W
R <sub>th j-a</sub>	Thermal Resistance, Junction to Ambient	71.4	°C/W
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature Range	-55~150	°C

**ELECTRICAL CHARACTERISTICS**

 T<sub>c</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = -30mA; I <sub>B</sub> = 0	-100			V
V <sub>CE(sat)-1</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> =-4A; I <sub>B</sub> = -16mA			-2.0	V
V <sub>CE(sat)-2</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> =-8A; I <sub>B</sub> = -80mA			-4.0	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> =-8A; I <sub>B</sub> = -80mA			-4.5	V
V <sub>BE(ON)</sub>	Base-Emitter voltage	I <sub>C</sub> = -4A; V <sub>CE</sub> = -4V			-2.8	V
I <sub>CEO</sub>	Collector Cutoff Current	V <sub>CE</sub> =-50V; I <sub>E</sub> = 0			-10	uA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> =-5V; I <sub>C</sub> = 0			-2	mA
h <sub>FE1</sub>	DC Current Gain	I <sub>C</sub> = -4A; V <sub>CE</sub> =- 4V	1000		12000	
h <sub>FE2</sub>	DC Current Gain	I <sub>C</sub> =-8A; V <sub>CE</sub> = -4V	100			
f <sub>T</sub>	Current-Gain—Bandwidth Product	I <sub>C</sub> =-3A; V <sub>CE</sub> =- 4V	4			MHz
C <sub>OB</sub>	Output Capacitance	I <sub>E</sub> =0; V <sub>CB</sub> = -10V; f= 1.0MHz		300		pF

Package Dimensions



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